2SC5390

Silicon NPN Epitaxial High Frequency Amplifier

HITACHI

ADE-208-492 (Z) 1st. Edition December. 1996

Features

- Excellent high frequency characteristics $f_T = 1.4 GHz$ (typ.)
- Low output capacitance C_{ob} = 2.4 pF (typ.)
- Isolated package TO–126FM

Outline

TO-126FM 1. Emitter 2. Collector 3. Base

2SC5390

Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

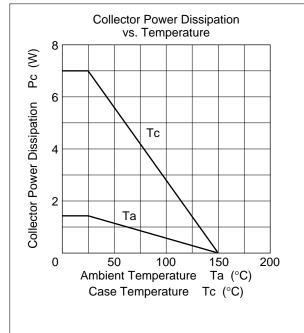
Item	Symbol	Ratings	Unit ∨	
Collector to base voltage	V_{CBO}	110		
Collector to emitter voltage	V_{CEO}	110	V	
Emitter to base voltage	V_{EBO}	3	V	
Collector current	I _c	200	mA	-
Collector peak current	İ _{c(peak)}	400	mA	
Collector power dissipation	P _c	1.4	W	
Collector power dissipation	P _c *1	7	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

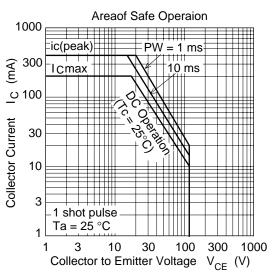
Note: 1. Value at Tc = 25°C

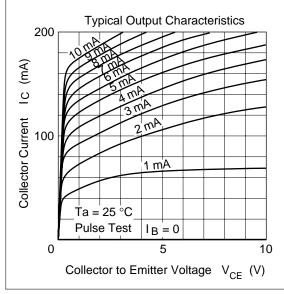
Electrical Characteristics ($Ta = 25^{\circ}C$)

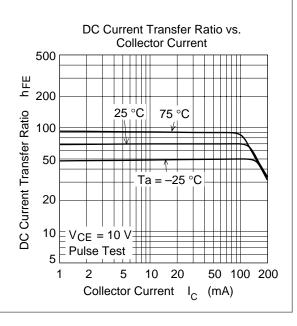
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	110	_	_	V	$I_{\rm C} = 10 \acute{\rm E} \ A, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	110	_	_	V	$I_{c} = 1 \text{mA}, R_{BE} = \infty$
Collector cutoff current	I _{CBO}			10	μΑ	$V_{CB} = 100V, I_{E} = 0$
Emitter cutoff current	I _{EBO}			10	μΑ	$V_{EB} = 3V, I_{C} = 0$
DC current transfer ratio	h _{FE}	30		100		$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{mA}$
Base to emitter voltage	V_{BE}			1	V	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{mA}$
Collector to emitter saturation voltage	V _{CE(sat)}	_	_	1	V	$I_{\rm C} = 200 \text{mA}, I_{\rm B} = 20 \text{mA}$
Gain bandwidth product	f _T	1.0	1.4	_	GHz	$V_{CE} = 10 \text{ V}, I_{C} = 50 \text{mA}$
Collector Output capacitance	C _{ob}		2.4	3.5	pF	$V_{CB} = 30V, I_{E} = 0$ f = 1MHz

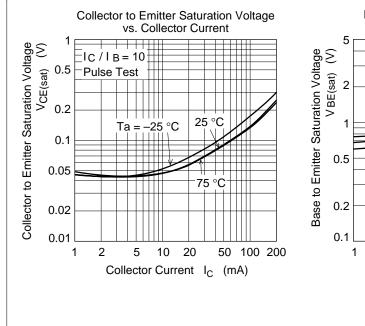
Main Characteristics

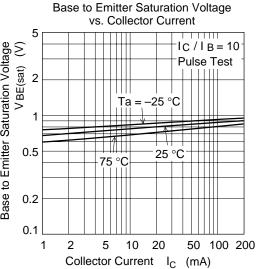


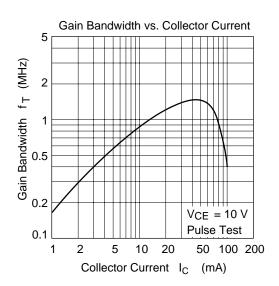


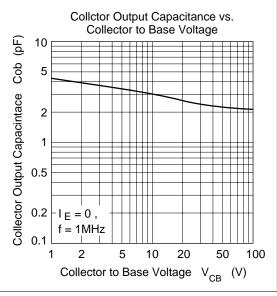






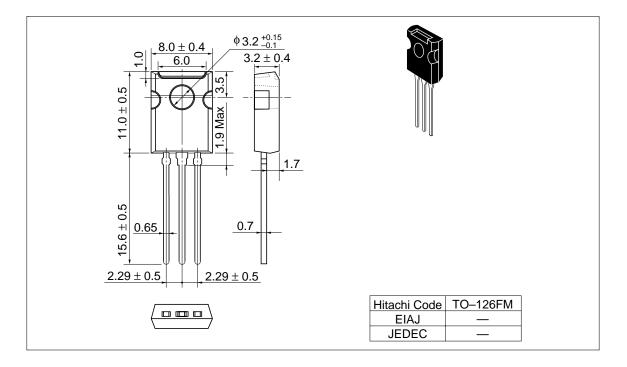






Package Dimentions

Unit: mm



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